Abstract

Memory element for a semiconductor memory device

A design of a memory element (1) is proposed, in which a number of material areas (N) which are isolated from one another are formed in order to form at least one area (B1, ..., B4) with changed electrical and/or magnetic characteristics in an isolation area (GOX) which is provided, which material areas (N) have or form free charge carriers. An information unit can correspondingly be written to, deleted and/or read from by influencing the material areas (N), by applying an electrical potential to line devices (BL1, ..., BL4) which are provided in areas (B1, ..., B4).

(Figure 1)



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